

## 30V N-Channel MOSFET



SOT-23

#### Pin Definition:

- 3 1 2
- 1. Gate
- 2. Source
- 3. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
30	30 @ V <sub>GS</sub> = 10V	5.8	
	43 @ V <sub>GS</sub> = 4.5V	5.0	

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

#### **Application**

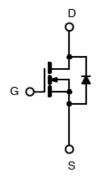
- Load Switch
- PA Switch

#### **Ordering Information**

Part No.	Package	Packing	
TSM3404CX RFG	SOT-23	3Kpcs / 7" Reel	

Note: "G" denotes Halogen Free Product.

#### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current		I <sub>D</sub>	5.8	А	
Pulsed Drain Current		I <sub>DM</sub>	20	А	
Continuous Source Current (Diode C	Conduction) <sup>a,b</sup>	) I <sub>S</sub> 2.		А	
Maximum Power Dissipation	Ta = 25°C		0.75	W	
	Ta = 75°C	$P_{D}$	0.48		
Operating Junction Temperature		T <sub>J</sub>	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit		
Junction to Foot Thermal Resistance	$R\Theta_{JF}$	75	°C/W		
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	140	°C/W		

#### Notes

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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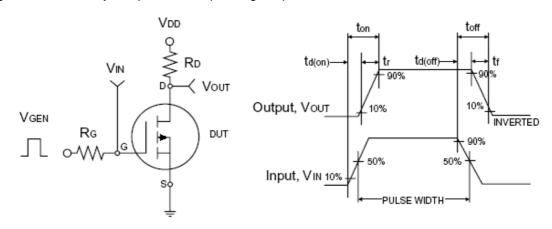


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		•				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30		1	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.4	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	μΑ
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μΑ
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	20		1	Α
Desir Course On Otata Basistana	$V_{GS} = 10V, I_D = 5.8A$	_		23	30	
Drain-Source On-State Resistance	rain-Source On-State Resistance $V_{GS} = 4.5V$ , $I_D = 5A$ $R_{DS(ON)}$		35	43	mΩ	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 5A$	g <sub>fs</sub>		25		S
Diode Forward Voltage	$I_S = 1.0A, V_{GS} = 0V$	V <sub>SD</sub>		0.76	1	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 15V, I_D = 5.8A,$ $V_{GS} = 10V$	$Q_g$		4.52		
Gate-Source Charge		$Q_gs$		1.24		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_gd$		1.68		
Input Capacitance	\/ 45\/ \/ 0\/	C <sub>iss</sub>		400.96		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	$C_{oss}$		100.47	1	pF
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		71.82	1	
Switching <sup>c</sup>						
Turn-On Delay Time	V 45V D 000	t <sub>d(on)</sub>		7.42		
Turn-On Rise Time	$V_{DD} = 15V, R_L = 2.2\Omega,$	t <sub>r</sub>		3.41		
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$	t <sub>d(off)</sub>		20.4		nS
Turn-Off Fall Time	$R_G = 6\Omega$	t <sub>f</sub>		3.01		

#### Notes:

- a. pulse test: PW  $\leq$ 300µS, duty cycle  $\leq$ 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

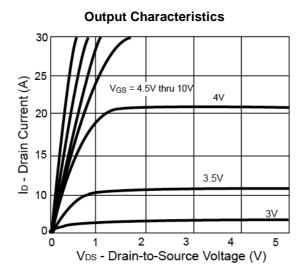
Switchin Waveforms



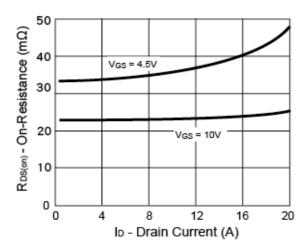
## 30V N-Channel MOSFET



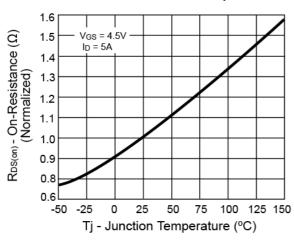
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



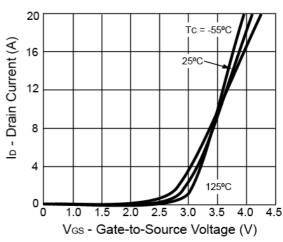
#### On-Resistance vs. Drain Current



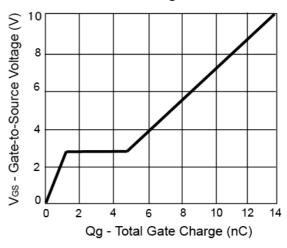
On-Resistance vs. Junction Temperature



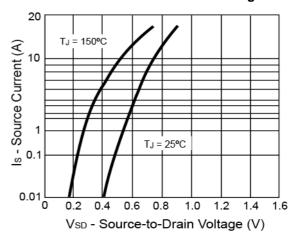
#### **Transfer Characteristics**



**Gate Charge** 



**Source-Drain Diode Forward Voltage** 



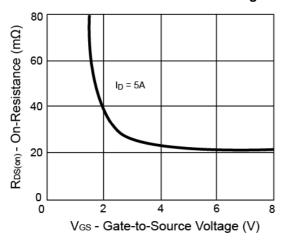


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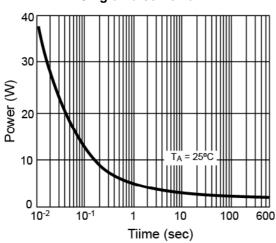
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage

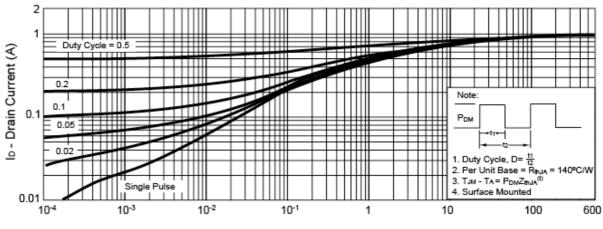


#### **Threshold Voltage** 0.2 0.1 Vgs(th) - Variance (V) I<sub>D</sub> = 1mA -0.0 -0.1 -0.2 -0.3 -50 -25 25 50 75 100 125 150 Tj - Junction Temperature (°C)

#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



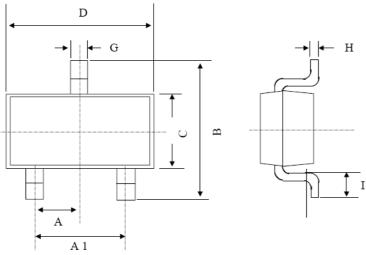
Square Wave Pulse Duration (sec)



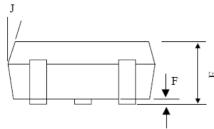
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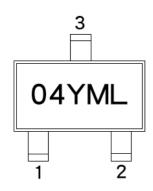
# **SOT-23 Mechanical Drawing**



OOT OO DIMENIOLONI					
SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
וווט	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037	BSC	
A1	1.9	BSC	0.074	74 BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
E	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
Ī	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



## **Marking Diagram**



04 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



# **TSM3404** 30V N-Channel MOSFET

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